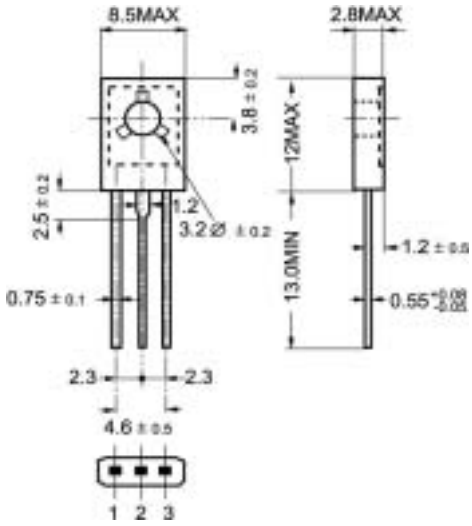
BD680

Silicon PNP Transistors

E C B

◆ Features

- With TO-126 package
- In monolithic Darlington configuration
- This transistor is intended for use in medium power linar and switching applications
- Complement to type BD679



TO-126

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	80	V
V_{CEO}	Collector to emitter voltage	80	V
V_{CER}	Emitter to base voltage		
V_{EB}	Emitter to base voltage	5	V
I_B	Base Current		
I_C	Collector current-Continuous	4	A
P_D	Total Power Dissipation@TC=25℃	40	W
T_j	Junction temperature	150	℃
T_{stg}	Storage temperature	-55~150	℃

◆ Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C=50mA; I_B=0	80		V
V_{CBO}	Collector-Base Voltage				
I_{CEO}	Collector Cutoff Current	V_{CE}=40V; I_B=0		500	uA
I_{CBO}	Collector Cutoff Current	V_{CB}=80V; I_E=0		200	uA
I_{EBO}	Emitter Cutoff Current	V_{EB}=5V; I_C=0		2	mA
V_{EBO}	Emitter Cutoff Current				
$V_{CE(sat-1)}$	Collector-emitter saturation voltages	I_C=1.5A; I_B=30mA		2.5	V
$V_{CE(sat-2)}$	Collector-emitter saturation voltages				
$V_{CE(sat-3)}$	Collector-emitter saturation voltages				
h_{FE-1}	Forward current transfer ratio	I_C=1.5A; V_{CE}=3V	750		
h_{FE-2}	Forward current transfer ratio				
$V_{BE(sat-1)}$	Base-Emitter Saturation Voltage				
$V_{BE(sat-2)}$	Base-Emitter Saturation Voltage				
f_T	Current Gain-Bandwidth Product				